

AMENDMENTS

In the Claims:

Please add new claim 16.

Please amend claims 1, 4 and 13-15 as follows:

Sub
C1
B1

1. (Amended) A gallium nitride compound semiconductor light-emitting diode comprising:

- a substrate;
- an n-type electrode region comprising an n-type transmissive electrode;
- a gallium nitride compound semiconductor multilayer structure including an active layer; and
- a p-type electrode region comprising a p-type transmissive electrode, wherein the n-type transmissive electrode and p-type transmissive electrode are thin films so as to be substantially transparent.

B2

4. (Amended) A gallium nitride compound semiconductor light-emitting diode according to claim 1, wherein the n-type transmissive electrode is formed around a circumference of the p-type transmissive electrode.

B3
and

13. (Amended) A gallium nitride compound semiconductor light-emitting diode comprising:

- a substrate;
- an n-type electrode region comprising an n-type transmissive electrode;
- a gallium nitride compound semiconductor multilayer structure including an active layer;
- and
- a p-type electrode region comprising a p-type transmissive electrode, wherein the n-type transmissive electrode is formed on a side face of the substrate, a side face of the buffer layer, and a side face of the n-type gallium nitride compound semiconductor layer in a region neighboring the buffer layer.

BB
cont.

14. (Amended) A gallium nitride compound semiconductor light emitting diode comprising:

- a substrate;
- an n-type electrode region comprising an n-type transmissive electrode;
- a buffer layer provided on the substrate;
- a gallium nitride compound semiconductor multilayer structure including an active layer provided on the buffer layer; and
- a p-type electrode region comprising a p-type transmissive electrode provided on the gallium nitride compound semiconductor multilayer structure, wherein the n-type transmissive electrode is formed on the lower face of the substrate, a side face of the substrate, a side face of the buffer layer, and a side face of the n-type gallium nitride compound semiconductor multilayer structure in a region neighboring the buffer layer, and wherein the n-type transmissive electrode comprises an oxide semiconductor.

15. (Amended) A gallium nitride compound semiconductor light-emitting diode comprising:

- a substrate;
- an n-type electrode region comprising an n-type transmissive electrode;
- a gallium nitride compound semiconductor multilayer structure including an active layer; and
- a p-type electrode region comprising a p-type transmissive electrode, wherein the n-type transmissive electrode and p-type transmissive electrode are films so as to be substantially transparent, and wherein the n-type transmissive electrode comprises a thick film of ITO.

B4

16. (New) A gallium nitride compound semiconductor light-emitting diode according to claim 4, wherein the n-type transmissive electrode is formed completely around the circumference of the p-type transmissive electrode.